

LLSD101A THRU LLSD101C

Schottky Barrier Switching Diode

Features

- Guard Ring Construction for Transient Protection
- Low Reverse Capacitance
- Low Forward Voltage Drop and Low Reverse Recovery Time
- Lead Free Finish/RoHS Compliant(Note 1) ("P" Suffix designates Compliant. See ordering information)

Mechanical Data

- Case: MiniMELF, Glass
- Terminals: Solderable per MIL-STD-202, Method 208
- Polarity: Indicated by Cathode Band
- Weight: 0.05 grams (approx.)

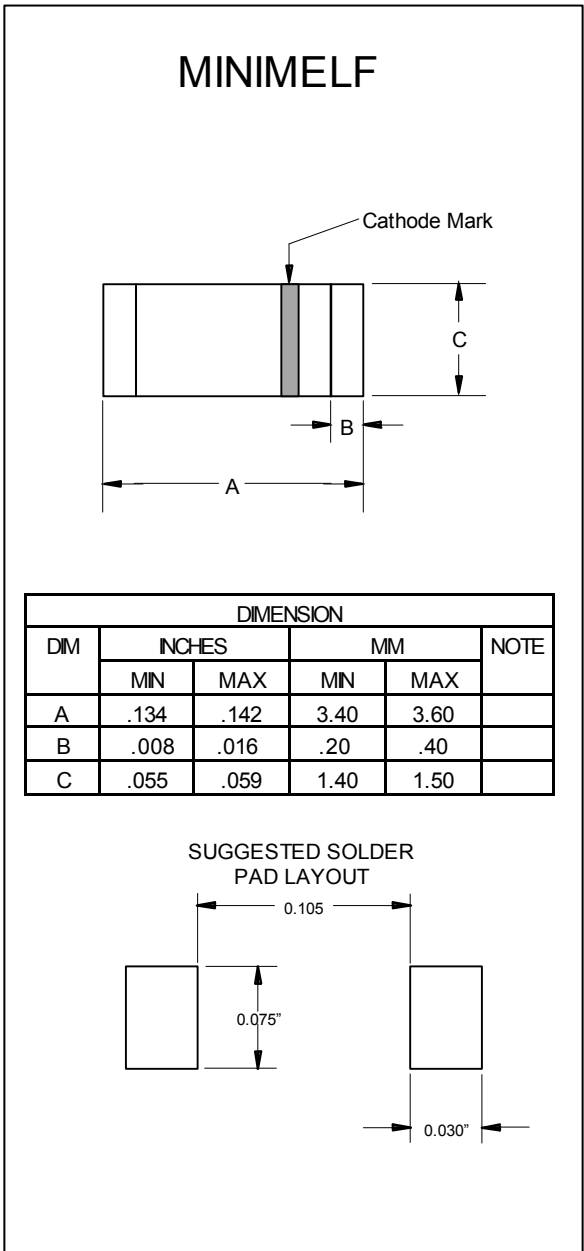
Maximum Ratings @ 25°C Unless Otherwise Specified

Characteristic	Symbol	LLSD101A	LLSD101B	LLSD101C
Peak Repetitive Reverse Voltage	V_{RRM}			
Working Peak Reverse Voltage	V_{RWM}	60V	50V	40V
DC Blocking Voltage	V_R			
RMS Reverse Voltage	$V_{R(RMS)}$	42V	35V	28V
Forward Continuous Current(Note 2)	I_{FM}	15mA		
Non-Repetitive Peak @ $t \leq 1.0s$ Forward Surge Current @ $t = 10\mu s$	I_{FSM}	50mA 2.0A		
Power Dissipation(Note 2)	P_d	400mW		
Thermal Resistance(Note 2)	R	375K/W		
Operation & Storage Temp. Range	T_j, T_{STG}	-55 to 150°C		

Electrical Characteristics @ 25°C Unless Otherwise Specified

Characteristic	Symbol	Min	Max	Unit	Test Cond.
Peak Reverse Current	I_{RM}	-----	200	nA	$V_R = 50V$ $V_R = 40V$ $V_R = 30V$
Forward Volt. Drop	V_{FM}	-----	0.41 0.40 0.39 1.00 0.95 0.90	V	$I_F = 1.0mA$ $I_F = 1.0mA$ $I_F = 1.0mA$ $I_F = 15mA$ $I_F = 15mA$ $I_F = 15mA$
Junction Capacitance	C_j	-----	2.0 2.1 2.2	pF	$V_R = 0V, f = 1.0MHz$
Reverse Recovery Time	t_{rr}	-----	1.0	ns	$I_F = I_R = 5mA,$ recover to $0.1 I_R$

Note: 1. Lead in Glass Exemption Applied, see EU Directive Annex 5.
2. Valid provided that electrodes are kept at ambient temperature



LLSD101A thru LLSD101C

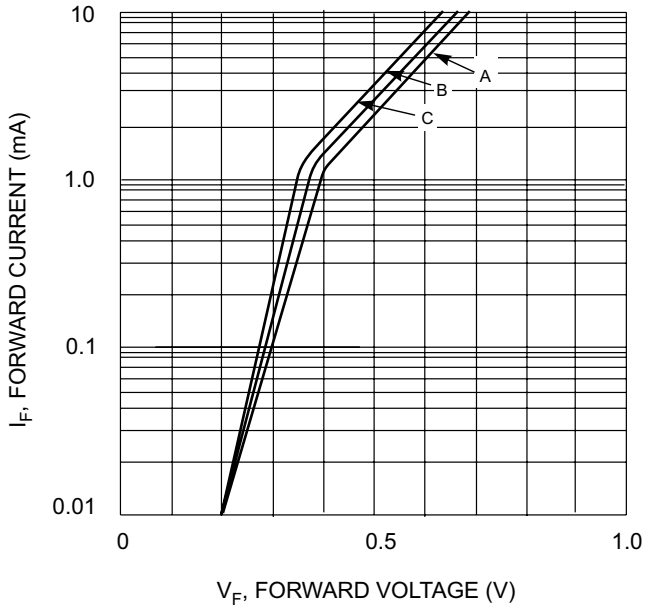


Fig. 1 Typical Forward Characteristic Variations for Primary Conduction

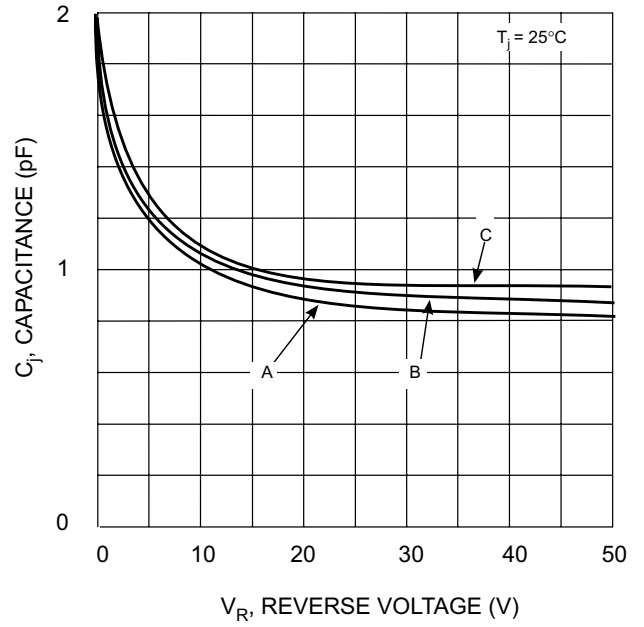


Fig. 2 Typ. Junction Capacitance vs Reverse Voltage

Ordering Information

Device	Packing
(Part Number)-TP	Tape&Reel;2.5Kpcs/Reel

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